

Description

- General purpose transistor

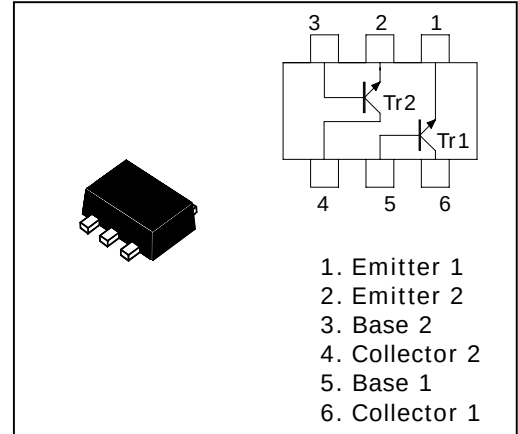
Outline

Feature

- Two 2SC5343 chips in SOT-563F package

Ordering Information

Type No.	Marking	Package Code
SUT507EF	6X	SOT-563F



Absolute maximum ratings (Tr1, Tr2 : NPN)

Ta=25°C

Characteristic	Symbol	Ratings	Unit
Collector-Base voltage	V_{CBO}	60	V
Collector-Emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	150	mA
Collector dissipation	P_C	100	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55 ~ 150	°C

Electrical Characteristics(Tr1,Tr2 : NPN)

Ta=25°C

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base breakdown voltage	BV_{CBO}	$I_C=100\mu A, I_E=0$	60	-	-	V
Collector-Emitter breakdown voltage	BV_{CEO}	$I_C=10mA, I_B=0$	50	-	-	V
Emitter-Base breakdown voltage	BV_{EBO}	$I_E=10\mu A, I_C=0$	5	-	-	V
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$	-	-	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	0.1	μA
DC current gain	h_{FE}	$V_{CE}=6V, I_C=2mA$	70	-	700	-
Collector-Emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$	-	-	0.25	V
Transition frequency	f_T	$V_{CE}=10V, I_C=1mA, f=100MHz$	80	-	-	MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	-	2	3.5	pF

Electrical Characteristic Curves

Tr1, Tr2 : NPN

Fig. 1 $I_C - V_{BE}$

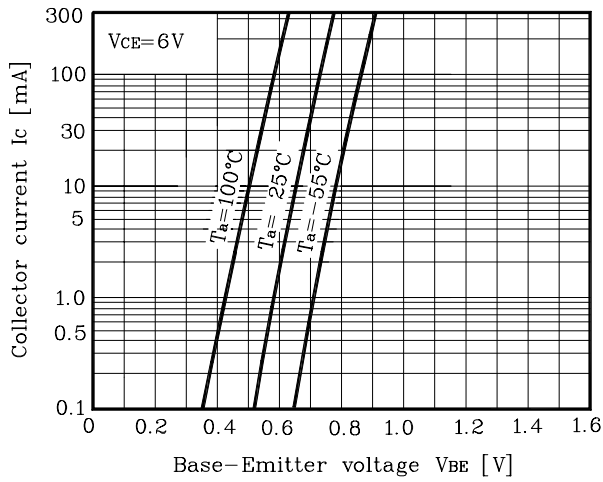


Fig. 2 $I_C - V_{CE}$

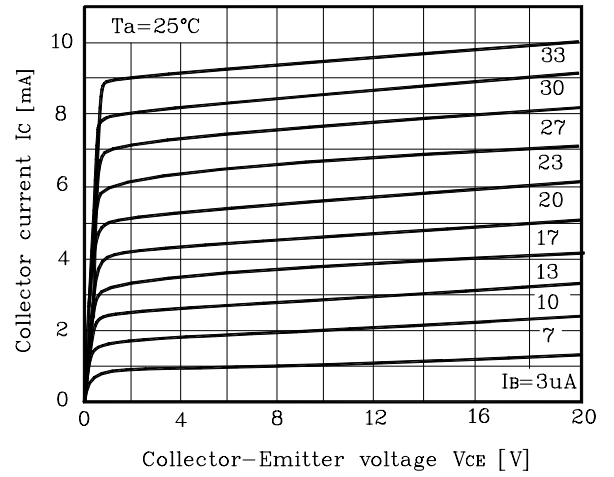


Fig. 3 $h_{FE} - I_C$

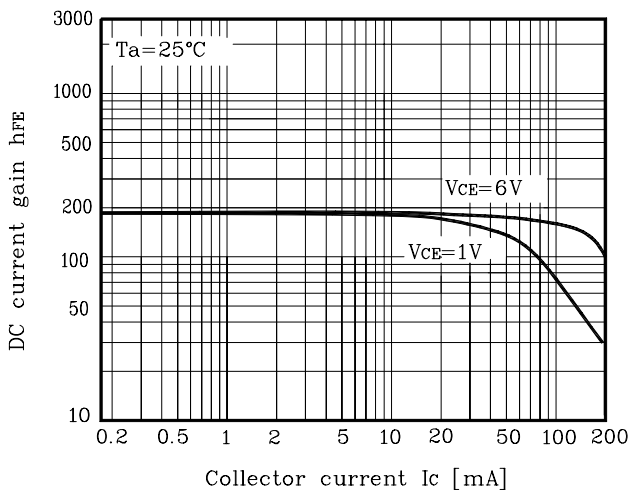


Fig. 4 $V_{CE(sat)} - I_C$

